

Silicon Diodes

Silicon Junction Diodes in DO-7 glass encapsulation for general applications

Type	Maximum Ratings				Characteristics at $T_{amb} = 25^\circ\text{C}$				
	V_R V	I_0 mA	P_{tot} mW	T_j °C	I_F mA	I_R μA	@ V_R V	C pF	θ_{amb} °C/mW
BAY 17	15	200 ¹⁾	400 ¹⁾	150	> 100	0,01 (< 0,1)	12	1,2	< 0,31 ¹⁾
BAY 18	60	200 ¹⁾	400 ¹⁾	150	> 100	0,01 (< 0,1)	50	1,2	< 0,31 ¹⁾
BAY 19	120	200 ¹⁾	400 ¹⁾	150	> 100	0,02 (< 0,1)	100	1,2	< 0,31 ¹⁾
BAY 20	180	200 ¹⁾	400 ¹⁾	150	> 100	0,03 (< 0,1)	150	1,2	< 0,31 ¹⁾
BAY 21	350	200 ¹⁾	400 ¹⁾	150	> 100	0,03 (< 0,1)	300	1,2	< 0,31 ¹⁾
BA 170	20	150 ¹⁾	300 ¹⁾	150	> 80	< 3	15	—	< 0,41 ¹⁾

¹⁾Valid provided that connection leads are kept at a temperature of 25°C at a distance of 4mm from the case.

Silicon High-Voltage Junction Diodes in long glass encapsulation.

Type	Maximum Ratings			Characteristics at $T_{amb} = 25^\circ\text{C}$					
	V_R V	V_{RM} V	I_0 mA	T_j °C	I_F mA	I_R μA	@ V_R V	θ_{amb} °C/mW	
BAY 23	1000	1500	50	150	> 80	< 1	1000	< 0,42	
BAY 24	1500	2250	50	150	> 80	< 1	1500	< 0,42	
BAY 25	2000	3000	50	150	> 80	< 1	2000	< 0,42	
BAY 26	3000	4500	50	150	> 80	< 3	3000	< 0,42	

Silicon Diode in DO-7 glass encapsulation, suitable for the protection of telephone relay contacts. Guaranteed operation during breakdown region.

Type	Maximum Ratings							Characteristics at $T_{amb} = 25^\circ\text{C}$					
	I_{FM} mA	I_{RM} mA	mA	mA	mA	mA	P_{tot} mW	T_j °C	$V_{(BR)R}$ V	$V_{(BR)I}$ V	I_R μA	V_F V	
BAW 21	150	2000	2000	100	4	2	2	200	150	90 ... 150	> 90	< 0,1	< 1,01

Silicon Diode in epoxy encapsulation for high speed switching e.g. diode clamping in colour TV.

Type	Maximum Ratings				Characteristics at $T_{amb} = 25^\circ\text{C}$				
	V_R V	V_{RM} V	I_F mA	I_{FM} mA	V_F V	I_R μA	t_{rr} ns	C pF	
BA 157	400	400	100	500	< 1	< 1	< 300	3	

Red = New Type